

L Number	Hits	Search Text	DB	Time stamp
1	670	wafer with chamber with cooling	USPAT; EPO; JPO	2002/09/30 13:44
5	23	(wafer with chamber with cooling) with ((reactant reactive source) adj3 gas\$2)	USPAT; EPO; JPO	2002/09/30 13:45
-	388700	argon helium nitrogen	USPAT	2002/09/27 13:47
-	970227	oxygen ammonia TaETO "nitrogen monoxide" "Nitrogen oxide" "Mononitrogen" monoxide "Nitric oxide" "Nitrous Oxide" "dinitrogen monoxide" "hyponitrous acid" "anhydride Nitrogen Oxide" "Dinitrogen oxide"	USPAT	2002/03/02 16:26
-	330656	"dihydrogen oxide" "Hydrogen oxide" Water (argon helium nitrogen) and (oxygen ammonia TaETO "nitrogen monoxide" "Nitrogen oxide" "Mononitrogen" monoxide "Nitric oxide" "Nitrous Oxide" "dinitrogen monoxide" "hyponitrous acid" "anhydride Nitrogen Oxide" "Dinitrogen oxide"	USPAT	2002/03/02 16:26
-	2983	"dihydrogen oxide" "Hydrogen oxide" Water ) ((argon helium nitrogen) and (oxygen ammonia TaETO "nitrogen monoxide" "Nitrogen oxide" "Mononitrogen" monoxide "Nitric oxide" "Nitrous Oxide" "dinitrogen monoxide" "hyponitrous acid" "anhydride Nitrogen Oxide" "Dinitrogen oxide"	USPAT	2002/03/02 16:27
-	2983	"dihydrogen oxide" "Hydrogen oxide" Water ) and "vacuum pressure" (((argon helium nitrogen) and (oxygen ammonia TaETO "nitrogen monoxide" "Nitrogen oxide" "Mononitrogen" monoxide "Nitric oxide" "Nitrous Oxide" "dinitrogen monoxide" "hyponitrous acid" "anhydride Nitrogen Oxide" "Dinitrogen oxide"	USPAT	2002/03/02 16:35
-	13	"dihydrogen oxide" "Hydrogen oxide" Water ) and "vacuum pressure") and vacuum (((argon helium nitrogen) and (oxygen ammonia TaETO "nitrogen monoxide" "Nitrogen oxide" "Mononitrogen" monoxide "Nitric oxide" "Nitrous Oxide" "dinitrogen monoxide" "hyponitrous acid" "anhydride Nitrogen Oxide" "Dinitrogen oxide"	USPAT	2002/03/02 16:28
		"dihydrogen oxide" "Hydrogen oxide" Water ) and "vacuum pressure") and vacuum) and (dilut\$3 near nitrogen)		

-	535039	(((argon helium nitrogen) and (oxygen ammonia TaETO "nitrogen monoxide" "Nitrogen oxide" "Mononitrogen" monoxide "Nitric oxide" "Nitrous Oxide" "dinitrogen monoxide" "hyponitrous acid" "anhydride Nitrogen Oxide" "Dinitrogen oxide" "dihydrogen oxide" "Hydrogen oxide" Water )) and "vacuum pressure") and vacuum) and ultra thin	USPAT	2002/03/02 16:33
-	354	(((argon helium nitrogen) and (oxygen ammonia TaETO "nitrogen monoxide" "Nitrogen oxide" "Mononitrogen" monoxide "Nitric oxide" "Nitrous Oxide" "dinitrogen monoxide" "hyponitrous acid" "anhydride Nitrogen Oxide" "Dinitrogen oxide" "dihydrogen oxide" "Hydrogen oxide" Water )) and "vacuum pressure") and vacuum and ultra	USPAT	2002/03/02 16:34
-	59	(((argon helium nitrogen) and (oxygen ammonia TaETO "nitrogen monoxide" "Nitrogen oxide" "Mononitrogen" monoxide "Nitric oxide" "Nitrous Oxide" "dinitrogen monoxide" "hyponitrous acid" "anhydride Nitrogen Oxide" "Dinitrogen oxide" "dihydrogen oxide" "Hydrogen oxide" Water )) and "vacuum pressure") and vacuum and LPCVD	USPAT	2002/03/02 16:35
-	57	(((argon helium nitrogen) and (oxygen ammonia TaETO "nitrogen monoxide" "Nitrogen oxide" "Mononitrogen" monoxide "Nitric oxide" "Nitrous Oxide" "dinitrogen monoxide" "hyponitrous acid" "anhydride Nitrogen Oxide" "Dinitrogen oxide" "dihydrogen oxide" "Hydrogen oxide" Water )) and "vacuum pressure") and vacuum and LPCVD) and temperature	USPAT	2002/03/02 16:35
-	2149	unload\$3 near (wafer substrate semiconductor)	USPAT; US-PGPUB; EPO; JPO	2002/09/27 13:50
-	1148	(unload\$3 near (wafer substrate semiconductor)) and temperature	USPAT; US-PGPUB; EPO; JPO	2002/09/27 13:51
-	50	((unload\$3 near (wafer substrate semiconductor)) and temperature) and ((steady adj3 state) "steady state")	USPAT; US-PGPUB; EPO; JPO	2002/09/27 15:02
-	308	cluster adj2 tools	USPAT; US-PGPUB; EPO; JPO	2002/09/27 15:03
-	120	(cluster adj2 tools) and cooling	USPAT; US-PGPUB; EPO; JPO	2002/09/27 15:25
-	175	bonderer.xa.	USPAT; US-PGPUB; EPO; JPO	2002/09/27 15:26
-	157	kilday.xa.	USPAT; US-PGPUB; EPO; JPO	2002/09/27 15:42